

Contents

1	Introduction	1
1.1	Preamble and Basic Definitions	1
1.2	Origins of Impurities and Defects	4
1.2.1	Natural Occurrence	4
1.2.2	Contamination	6
1.2.3	Doping	8
1.2.4	Growth, Thermal Treatments and Irradiation	9
	1.2.4.1 Growth and Thermal Treatments.....	9
	1.2.4.2 Radiation Defects	10
1.3	Structural Properties	12
1.3.1	Global Atomic Configurations	12
1.3.2	Lattice Distortion and Metastability.....	16
1.4	Physico-chemical Properties	18
1.4.1	Solubilities	18
1.4.2	Diffusion Coefficients.....	20
1.5	Electrical Activity.....	22
1.5.1	Donors and Acceptors	22
1.5.2	Compensation	24
1.5.3	Passivation.....	25
1.5.4	Deep Levels and Negative- <i>U</i> Properties	26
1.5.5	Transition Metals.....	28
1.5.6	Attracting Isoelectronic Impurities	29
1.5.7	Lattice Point Defects.....	30
1.6	Optical Properties	31
1.6.1	Electronic Studies	31
1.6.2	Vibrations of Impurities and Defects	32
1.7	Spin Effects	34
1.8	Labelling of the Spectroscopic Signatures.....	35
	References	37

2 Bulk Optical Absorption	43
2.1 Introduction	43
2.2 Lattice Absorption	45
2.2.1 Fundamental Lattice Absorption	45
2.2.2 Multi-phonon Absorption and Anharmonicity	51
2.3 Electronic Absorption	56
2.3.1 Energy Gap and Intrinsic Absorption	56
2.3.1.1 Band Structure	56
2.3.1.2 Band Parameters	60
2.3.1.3 Absorption Coefficients	65
2.3.1.4 Band Gap Dependences	67
Temperature	67
Hydrostatic Pressure	70
Magnetic Field	72
Isotopic Composition	72
2.3.2 Excitons	74
2.3.3 Electron–Hole Droplets (EHDs), Biexcitons, and Polyexcitons	79
2.4 Conclusion	81
References	81
3 Instrumental Methods for Absorption Spectroscopy in Solids	89
3.1 Introduction	89
3.2 Spectrometer–Detector Combinations	94
3.3 Tunable Sources	99
3.4 Filtering and Polarization	100
3.5 Samples Conditioning	101
3.6 Cooling the Samples	102
3.7 Compressing the Samples	105
3.7.1 Uniaxial Stresses	105
3.7.2 Hydrostatic Stresses	107
3.8 Magneto-optical Measurements	109
References	110
4 Absorption of Deep Centres and Bound Excitons	113
4.1 Radiation Defects in Silicon	115
4.1.1 The Divacancy	116
4.1.2 The Higher Order Bands (HOBs)	125
4.1.3 Group V-related Defects and Li-related Defects	126
4.1.3.1 The Vacancy–Group V Pair	126
4.1.3.2 Other Group V-related Defects	127
4.1.3.3 Li-related Defects	128
4.1.4 Carbon-related Bands	130
4.1.4.1 Interstitial Carbon (C_i)	130
4.1.4.2 The G Line (969 meV Line) and the C_iSiC_s Defect	131

4.1.4.3	The <i>C</i> and <i>P</i> Lines	134
4.1.4.4	The 3942 cm ⁻¹ Line Defect	137
4.2	Impurity Centres and Defects in Diamond	137
4.2.1	Intrinsic Defects	139
4.2.1.1	Self-interstitial-related Centres	139
4.2.1.2	Vacancy-related Centres	140
4.2.1.3	Brown Diamonds	143
4.2.2	Nitrogen-related Centres	144
4.2.2.1	Substitutional and Vacancy-associated Centres ...	144
	Substitutional Nitrogen (N _s)	145
	The Substitutional N Pair (N _{2s})	
	(A Aggregate or A Centre)	146
	VN ₄ (B Aggregate or B Centre) and VN ₃	146
	The NV Centre	147
	VN ₂ and V ₂ N ₄	148
4.2.2.2	Other N-related centres	149
4.2.3	Si-related Absorption	149
4.3	EL2 in GaAs	152
4.3.1	EL2 as a Double Donor	152
4.3.2	Photoinduced Metastability of EL2	152
4.3.3	Optical Absorption	153
4.3.4	Other Optical Properties	156
4.4	Transition Metal (TM) Impurities	158
4.4.1	Introduction	158
4.4.2	Generalities on TM Impurities	158
4.4.3	Intracentre Transitions	160
4.4.4	High- or Low-Spin Ground States?	165
4.4.5	Isotope Effects	166
4.4.6	Transitions Between TMs Energy Levels and Valence or Conduction Band	169
4.4.7	Transitions Involving Hydrogen-Like Hole States	171
	References	175
5	Vibrational Absorption of Substitutional Atoms and Related Centres	189
5.1	Introduction	189
5.2	Overview of Theoretical Methods	193
5.3	Vibrational Spectra of Specific Centres	194
5.3.1	Li, Group-II Atoms, and 3 <i>d</i> Transition Metals (TMs)	195
5.3.1.1	Li	195
5.3.1.2	Group-II Atoms	197
5.3.1.3	TM Atoms	200
5.3.2	C	201
5.3.2.1	Silicon and Germanium	201
5.3.2.2	III–V Compounds	203

5.3.3	B and Al	210
5.3.3.1	Group-IV Crystals	211
5.3.3.2	Compound Crystals	212
5.3.4	B Pairing with Donors	214
5.3.4.1	Group-IV Crystals	214
5.3.4.2	III-V Compounds	217
5.3.5	Si	217
5.3.6	N	221
5.3.6.1	Diamond	221
5.3.6.2	Other Group-IV Crystals	224
5.3.6.3	Other Semiconductors	226
5.3.7	P and As	227
5.3.8	O, S, and Se	228
5.3.8.1	III-V Compounds	228
5.3.8.2	II-VI Compounds	229
	References	233
6	Vibrational Absorption of O and N Interstitial Atoms and Related Centres	243
6.1	Bond-Centred O in Semiconductors	244
6.1.1	Interstitial Oxygen in Silicon	244
6.1.1.1	Isolated Oxygen (O_i)	244
	Frequencies	249
	Linewidths and Lifetimes	260
	Stress Effects and Reorientation	263
	O_i Perturbation by Ge and Sn Atoms	266
	Relative Intensities and Calibration	268
6.1.1.2	The Dimer (O_{2i}) and the TDDs	271
6.1.1.3	Oxygen Precipitation	276
6.1.1.4	O_i Interaction with Other Foreign Atoms	278
	Carbon	278
	Hydrogen	279
	Lithium	282
6.1.2	Interstitial Oxygen in Germanium	282
6.1.2.1	Isolated Oxygen (O_i)	282
	Frequencies	286
	Linewidths and Lifetimes	298
	Reorientation and Calibration	300
6.1.2.2	The Dimer (O_{2i}) and the TDDs	300
6.1.2.3	Oxygen Precipitation	305
6.1.3	Interstitial Oxygen in GaAs and GaP	306
6.2	Interstitial-N-related Centres	308
6.2.1	Diamond	308
6.2.2	Silicon and Germanium	310
6.2.2.1	The N_i - N_i Split Pair	310
6.2.2.2	Complexes with Oxygen	312

6.3	Some Interstitial Centres in III–V Compounds.....	315
6.4	Self-Interstitial-related Centres in Diamond.....	316
	References	316
7	Vibrational Absorption of Quasi-substitutional Atoms and Other Centres	325
7.1	Quasi-substitutional O (VO)	325
7.1.1	O-Vacancy Centres in Silicon	326
7.1.1.1	Isolated VO	326
7.1.1.2	V_nO_m Centres	332
7.1.1.3	VO and Foreign Atoms	334
7.1.2	VO in Germanium	337
7.1.3	Off-centre Oxygen (O_{oc}) in GaAs	340
7.2	C-Related Irradiation Defects	346
7.2.1	Interstitial Carbon (C_i), (IC_i) and (C_i , Sn_s) in Silicon	347
7.2.2	The C_iSiC_s Defect in Silicon	348
7.2.3	The Dicarbon nn Pair ($C_s - C_s$) in Silicon.....	352
7.2.4	The Carbon–Oxygen Centres in Silicon	353
7.2.4.1	The C_iO_i Centre [“C” or C(3) Centre].....	353
7.2.4.2	The (IC_iO_i) Centre	355
7.2.5	The C(1) Centre in GaAs and GaP	357
7.3	B-Related Irradiation Defects	359
7.3.1	Silicon	359
7.3.2	III–V Compounds	361
	References	362
8	Vibrational Absorption Associated with Hydrogen	369
8.1	Introduction	369
8.2	Intrinsic Hydrogen Centres	370
8.2.1	“Isolated” Hydrogen	370
8.2.1.1	Diamond	370
8.2.1.2	Silicon, Germanium, and SiGe Alloys.....	371
8.2.1.3	Compound Semiconductors	375
8.2.2	The Hydrogen Dimer H_2^*	376
8.2.3	Hydrogen and Vacancies.....	379
8.2.3.1	Group IV Semiconductors.....	379
8.2.3.2	Compound Semiconductors	384
8.2.4	Hydrogen and Self-Interstitials	388
8.3	Hydrogen Molecules.....	389
8.3.1	Reminder on Free Hydrogen Molecules	389
8.3.2	Isolated Molecules in GaAs	390
8.3.3	Isolated Molecules in Silicon	392
8.3.3.1	Raman Spectroscopy	393
8.3.3.2	Absorption Spectroscopy	394
8.3.3.3	Ortho–Para Conversion	395
8.3.4	Isolated Molecules in Germanium	396
8.3.5	Isolated Molecules in ZnO.....	396

8.3.6	Isolated Molecules in Gallium Nitride	397
8.3.7	Molecules Trapped by Oxygen in Silicon	399
8.3.8	Molecules in Platelets and Voids	399
8.4	Extrinsic Hydrogen Centres I	401
8.4.1	Isoelectronic Atoms	402
8.4.1.1	Carbon in Silicon and Germanium.....	402
	A Weakly Bound Centre	403
	The CH_2^* Dimers	404
	The Hydrogenated C_s Dicarbons Pair.....	405
8.4.1.2	Nitrogen in III–V Compounds	406
	GaP	407
	GaAs	409
8.4.1.3	III–V _{1–x} N _x Dilute Alloys.....	409
8.4.1.4	Discussion on (N, H) Complexes in III–V Compounds and Their Alloys	411
8.4.2	Interaction with C_i in Silicon	412
8.5	Extrinsic Hydrogen Centres II	413
8.5.1	(Acceptor, Hydrogen) Centres.....	413
8.5.1.1	Elemental Semiconductors	413
8.5.1.2	Compound Semiconductors	418
	III–V Compounds.....	418
	II–VI Compounds.....	425
8.5.1.3	Stress-induced Reorientation.....	427
8.5.2	(Donor, Hydrogen) Centres	430
8.5.2.1	Compound Semiconductors	431
	Donors on Cation Sites	431
	Donors on Anion Sites	433
8.5.2.2	Silicon	438
8.6	Hydrogen and Transition Metals (TMs)	440
8.6.1	Complexes with TMs in Silicon	440
8.6.2	Copper–Hydrogen Complexes in ZnO	442
8.6.3	TM–Hydrogen Complexes in III–V Compounds	443
8.7	Other H-Related Centres	445
8.7.1	Hydrogen-related LVMs in Diamond	445
8.7.2	(O, H) Centres in GaAs and GaP.....	447
8.7.2.1	The 3300 cm^{-1} Line in GaAs	447
8.7.2.2	Other (O,H) Centres in GaAs and GaP	448
8.7.3	“Hidden” Hydrogen in InP	449
8.7.4	Unidentified H-Related LVMs.....	450
	References	451
A	Energy Units Used in Spectroscopy and Solid-State Physics	465
A.1	Values of Selected Physical Constants Recommended by CODATA (2006)	466

B Bravais Lattices, Symmetry, and Crystals 467

 B.1 The Reciprocal Lattice 469

 B.2 Lattice Planes and Miller Indices 470

 B.3 A Toolbox for Symmetry Groups 471

 B.3.1 The Abstract Groups 471

 B.3.2 The Symmetry Point Groups 472

 B.3.3 Representations and Basis Functions 473

 B.3.4 The Symmetry Space Groups 476

 B.4 Some Crystal Structures 478

 B.4.1 Cubic Structures 478

 B.4.2 Hexagonal Structures 480

 References 482

C Optical Band Gaps and Crystal Structures of Some Insulators and Semiconductors 483

D Table of Isotopes 485

E Uniaxial Stress and Orientational Degeneracy 495

 References 499

Index 501